



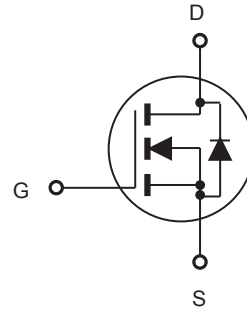
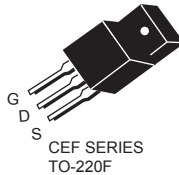
CEP1186/CEB1186 CEF1186

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

Type	V _{DSS}	R _{DS(ON)}	I _D	@V _{GS}
CEP1186	800V	2.3Ω	6A	10V
CEB1186	800V	2.3Ω	6A	10V
CEF1186	800V	2.3Ω	6A ^d	10V

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- Lead-free plating ; RoHS compliant.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263	TO-220F	
Drain-Source Voltage	V _{DS}	800		V
Gate-Source Voltage	V _{GS}	±30		V
Drain Current-Continuous	I _D	6	6 ^d	A
Drain Current-Pulsed ^a	I _{DM} ^e	24	24 ^d	A
Maximum Power Dissipation @ T _C = 25°C - Derate above 25°C	P _D	166	50	W
		1.3	0.4	W/°C
Single Pulsed Avalanche Energy ^h	E _{AS}	9.4		mJ
Single Pulsed Avalanche Current ^h	I _{AS}	2.5		A
Operating and Store Temperature Range	T _J , T _{stg}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	R _{θJC}	0.75	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	65	°C/W



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Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	800			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 800V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
On Characteristics ^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 2.5A$		1.9	2.3	Ω
Dynamic Characteristics ^c						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{ MHz}$		958		pF
Output Capacitance	C_{oss}			152		pF
Reverse Transfer Capacitance	C_{rss}			19		pF
Switching Characteristics ^c						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300V, I_D = 5A, V_{GS} = 10V, R_{GEN} = 25\Omega$		25	53	ns
Turn-On Rise Time	t_r			46	95	ns
Turn-Off Delay Time	$t_{d(off)}$			94	192	ns
Turn-Off Fall Time	t_f			24	56	ns
Total Gate Charge	Q_g	$V_{DS} = 480V, I_D = 5A, V_{GS} = 10V$		29.4	41.8	nC
Gate-Source Charge	Q_{gs}			5		nC
Gate-Drain Charge	Q_{gd}			11		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current	I_S^f				5	A
Drain-Source Diode Forward Voltage ^b	V_{SD}^g	$V_{GS} = 0V, I_S = 5A$			1.4	V
Notes : <input type="checkbox"/> a.Repetitive Rating : Pulse width limited by maximum junction temperature . b.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. <input type="checkbox"/> c.Guaranteed by design, not subject to production testing. <input type="checkbox"/> d.Limited only by maximum temperature allowed . e.Pulse width limited by safe operating area . f.Full package $I_{S(max)} = 3.2A$. g.Full package V_{SD} test condition $I_S = 3.2A$. <input type="checkbox"/> h.L = 3mH, $I_{AS} = 2.5A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25\text{ C}$						



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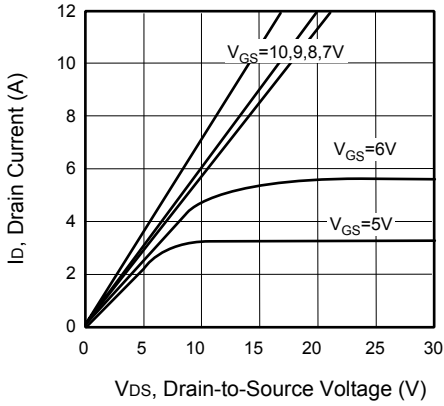


Figure 1. Output Characteristics

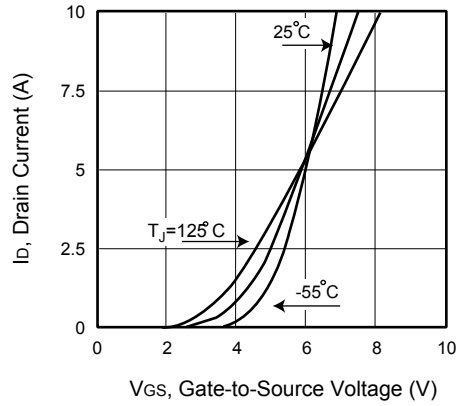


Figure 2. Transfer Characteristics

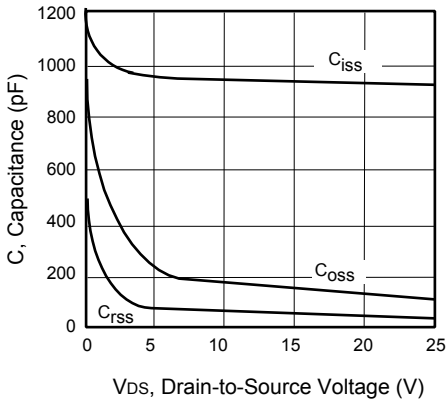


Figure 3. Capacitance

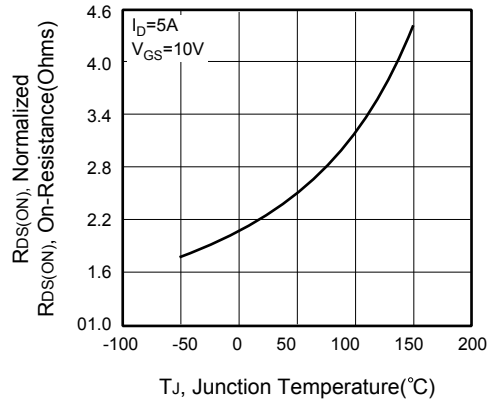


Figure 4. On-Resistance Variation with Temperature

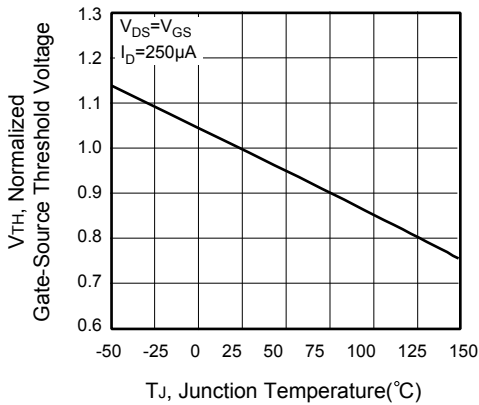


Figure 5. Gate Threshold Variation with Temperature

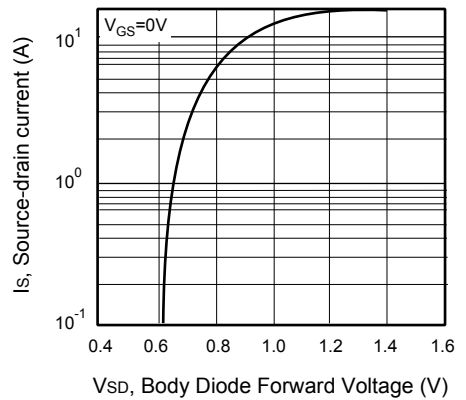


Figure 6. Body Diode Forward Voltage Variation with Source Current



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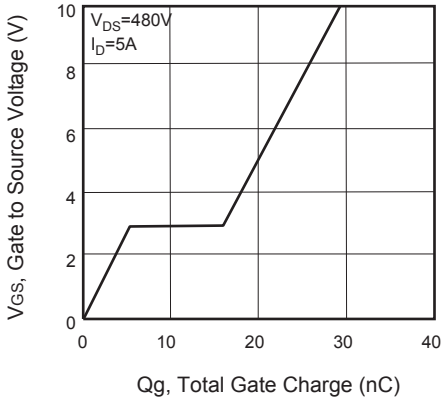


Figure 7. Gate Charge

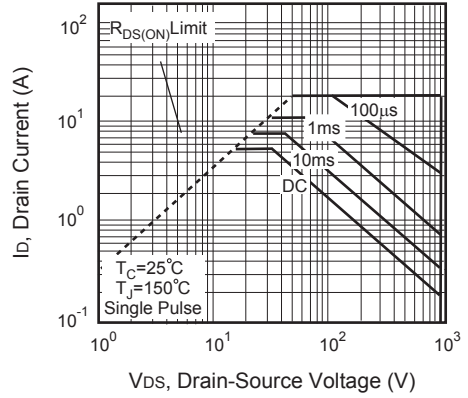


Figure 8. Maximum Safe Operating Area



Figure 9. Switching Test Circuit



Figure 10. Switching Waveforms

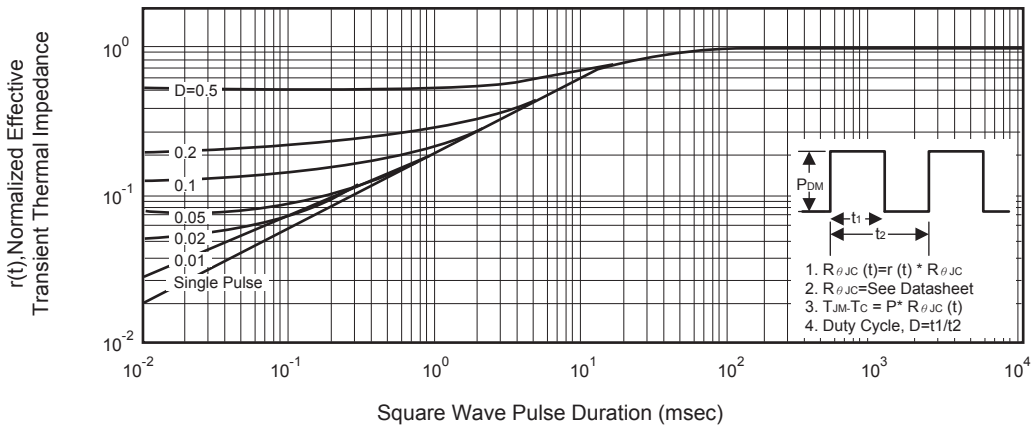


Figure 11. Normalized Thermal Transient Impedance Curve